
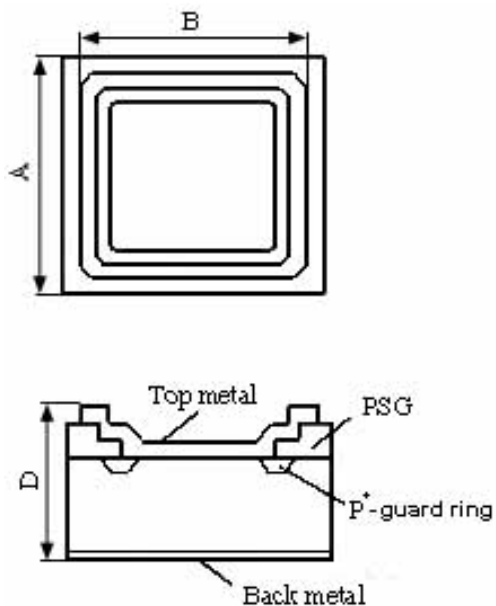


SCHOTTKY DIODES KDN-01040D.
PRELIMINARY



Rev.1. Feb. 2010

|  VSP-MIKRON | 1A/40V. Die Size-28mil. | | | |
|--|--------------------------------|-------------|--------------------|-----------------------|
| Electrical Characteristics | Symbol | Unit | Spec. limit | Die Sort |
| Breakdown Voltage @ $I_R=10mA$ | V_{BR} | V | 40 | 45 |
| Average Rectified Forward Current | $I_{F(AV)}$ | A | 1,0 | - |
| DC Forward Voltage @ 25°C, $I_F=1,0A$ | V_F | V | 0,60 | 0,58 |
| Maximum Reverse Current @ 25°C, $V_R=45V$ 25°C, $V_R=40V$ 125°C, $V_R=40V$ | I_R | mA | - 0,050 10,0 | 0,050 0,030 9,0 |
| Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD) | I_{FSM} | A | 20 | - |
| Peak Repetitive Reverse Surge Current @2,0µs, f=1kHz., $T_J<150°C$. | I_{RRM} | A | 1,0 | |
| Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact. | ESD | kV | ±8 (contact) | |
| Voltage Rate of Change | dV/dt | V/µS | 10.000 | |
| Operating Junction Temperature | T_J | °C | 150 | |



| DIM | ITEM | µm |
|-------------------|---------------------|------------|
| A_x A_y | Wafer Form Die Size | 720 720 |
| B_x B_y | Top Metal Size | 610 610 |
| D | Thickness | 300max. |
| Scribe line Width | | 80 |

Top metal: a) **Al** – for Wire Bonding;
b) **Al-Ni-Ag** – for Soldering.
Backside metal: **Ti-Ni-Ag**.